

Features

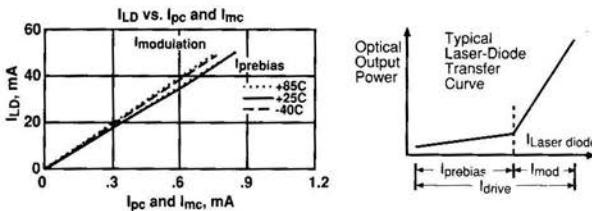
- High Data Rates: 1.5 Gb/s NRZ
- High Modulation Current: 50 mA
- High Prebias Current: 50 mA
- Low VSWR 50 Ω Input, ECL Level Compatible
- Differential or Single-ended Inputs
- Separate Modulation and Prebias Controls
- Single Power Supply: +5 V or -5.2 V
- Hermetic Glass-metal Surface Mount Package

Description

The IDA-07318 is a wideband silicon bipolar Monolithic Microwave Integrated Circuit (MMIC), Laser Diode (LD) driver, housed in a miniature glass-metal hermetic surface mount package. It is designed to provide high speed current drive for laser diodes or light emitting diodes (LEDs). On-chip termination resistors and flexible prebias and modulation control inputs simplify your design.

Typical applications include fiber optic data communications (e.g., FDDI, serial HIPPI) and telecommunications (e.g., SONET) systems where high speed laser diodes are used with data rates up to 1.5 Gb/s. In addition, instrumentation and communication circuits can use the high speed current modulation feature of the IDA-07138.

The IDA series of laser diode drivers is fabricated using HP's 10 GHz ft, 25 GHz f_{MAX} ISOSATTM-1 silicon bipolar process that uses nitride self-alignment, submicrometer lithography, trench isolation, ion implantation, gold metalization, and polyimide inter-metal dielectric and scratch protection to achieve excellent performance uniformity, and reliability.



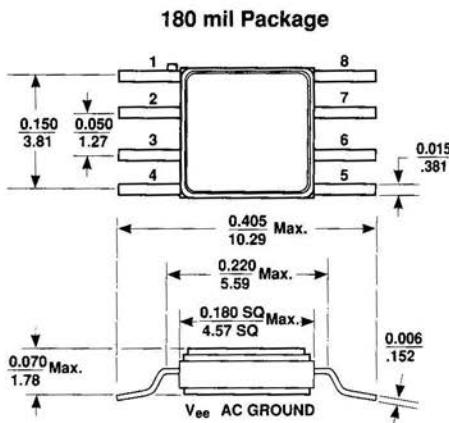
Guaranteed Electrical Specifications, $T_A = 25^\circ C$, $V_{cc} = 0 V$, $V_{ee} = -5.2 V$, Z Load = 12 Ω (see Test Configuration)

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
t_r	Output Rise Time, 20% to 80% (Pin 6) $I_{mod} = 25 \text{ mA}, I_{pb} = 50 \text{ mA}$	ps		220	300
t_f	Output Fall Time, 20% to 80% (Pin 6) $I_{mod} = 25 \text{ mA}, I_{pb} = 50 \text{ mA}$	ps		240	320
I_{pb}	Laser Diode Prebias Current Set Range	mA	0-50		
I_{mod}	Laser Diode Modulation Current Set Range ¹	mA	5-50		
I_d	Device Current $V_{cc} - V_{ee} = 5 \text{ V}, I_{mod} = 0 \text{ mA}, I_{pb} = 0 \text{ mA}$		30	40	50

Notes: 1. Recommended operating range for Modulation Current Set is 10 to 50 mA.

Design Information, $T_A = 25^\circ C$, $V_{cc} = 0 V$, $V_{ee} = -5.2 V$, Z Load = 12 Ω (see Test Configuration)

Symbol	Parameters and Test Conditions	Units	Typ.
t_p	Propagation Delay Time, Input to Output $I_{mod} = 25 \text{ mA}$	ps	300
BW	Small Signal -3 dB Bandwidth $I_{mod} = 25 \text{ mA}$	GHz	1.0
VSWR	V_{in+}, V_{in-} VSWR $f = 0.1 \text{ to } 2 \text{ GHz}$		2:1
$t_{pb}, t_{r, mod}$	Modulation or Prebias Current Output Rise Time (Inputs Pin 3 or 5)	ns	6

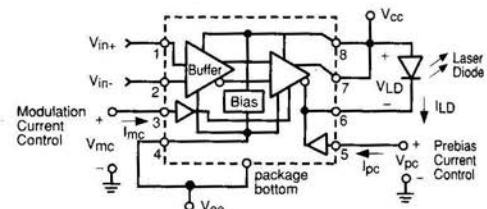


PIN DESCRIPTION	
1 Vin+	8 V _{cc}
2 Vin-	7 Output Current-
3 Mod. Input	6 Output Current+ (to LD)
4 V _{ee}	5 Prebias Input
Bottom of Package is V _{ee}	

Notes:
(unless otherwise specified)

1. Dimensions are in mm
2. Tolerances in $xxx = \pm 0.005$
mm $.xx = \pm .13$

Functional Block Diagram



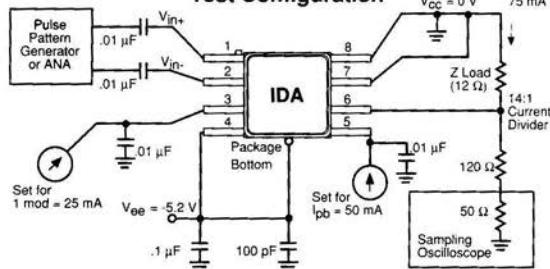
Absolute Maximum Ratings

Parameter	Absolute Maximum ¹
Device Voltage	10 V
Power Dissipation ^{2, 3}	2.5 W
I_{mod} or I_{pb}	150 mA rms
Junction Temperature	200°C
Storage Temperature	-65 to 200°C
Thermal Resistance ^{2, 3} : $\theta_{JC} = 50^\circ\text{C}/\text{W}$	

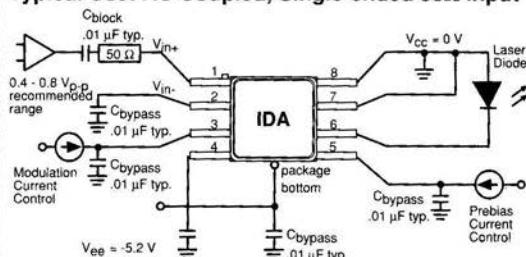
Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2. $T_{case} = 25^\circ\text{C}$
3. Derate at 20 mW/ $^\circ\text{C}$ for $T_C > 75^\circ\text{C}$

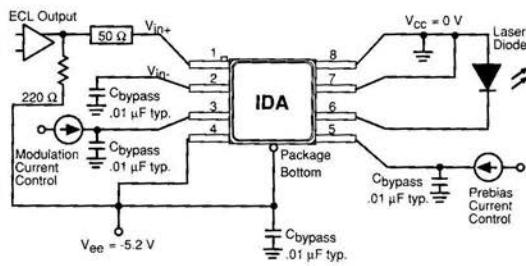
Test Configuration



Typical Use: AC Coupled, Single-ended 50Ω Input



Typical Use: DC Coupled, Single-ended ECL Input



Typical Performance, $T_A = 25^\circ\text{C}$

$V_{cc} = 0 \text{ V}$, $V_{ee} = 5.2 \text{ V}$, $R_L = 12 \Omega$
(unless otherwise noted)

